

NOT RECOMMENDED FOR NEW DESIGN **USE DMN2040U**



DMN2041L

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

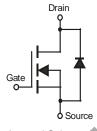
Mechanical Data

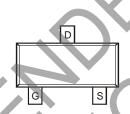
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Top View







Internal Schematic

Top View

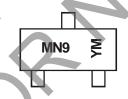
Ordering Information (Note 4)

-			
١	Part Number	Case	Packaging
	DMN2041L-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



MN9 = Product Type Marking Code YM or \(\overline{Y}\)M = Date Code Marking for SAT Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015	
Code	W		Х		Y		Z			В		С	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec	
Code	1	2	3	4	5	6	7	8	9	0	N	D	



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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characte	eristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 5)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	6.4 4.5	Α
Pulsed Drain Current (Note 6)			I _{DM}	30	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.78	W
Thermal Resistance, Junction to Ambient @ T _A = +25°C	R _{θJA}	161	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

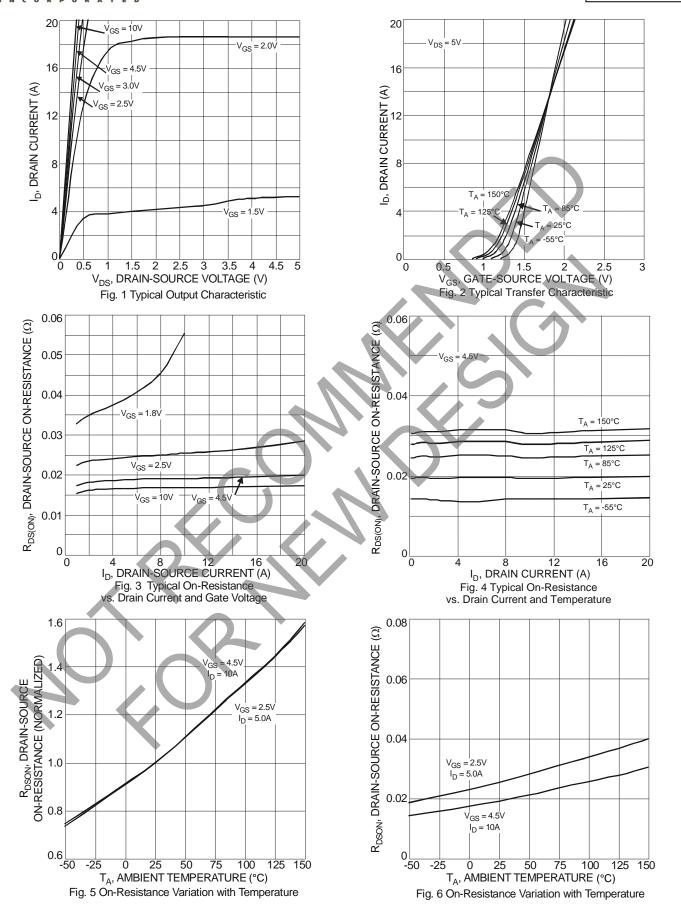
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition			
OFF CHARACTERISTICS (Note 7)									
Drain-Source Breakdown Voltage	BV _{DSS}	20	1		V	$V_{GS} = 0V, I_D = 250\mu A$			
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_		1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$			
Gate-Source Leakage	IGSS	-	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$			
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(TH)}	0.5		1.2	V	$V_{DS}=V_{GS},I_D=250\mu A$			
Static Drain-Source On-Resistance	Paramo	7	20	28	mΩ	$V_{GS} = 4.5V, I_D = 6.0A$			
Static Dialif-Source Off-Resistance	R _{DS(ON)}	1	26	41	11122	$V_{GS} = 2.5V, I_D = 5.2A$			
Forward Transfer Admittance	Y _{fs}		6	_	S	$V_{DS} = 10V, I_D = 6A$			
Diode Forward Voltage	V _{SD}		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.7A$			
DYNAMIC CHARACTERISTICS (Note 8)									
Input Capacitance	C _{iss}	_	550	_		$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz			
Output Capacitance	Coss	_	88	_	pF				
Reverse Transfer Capacitance	C _{rss}	1	81	_		1 – 1.01/11/12			
Gate Resistance	R_g	-	1.34	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$			
Total Gate Charge (10V)	Qg	_	15.6	_	nC	$V_{GS} = 10V, V_{DS} = 10V, I_D = 6A$			
Total Gate Charge (4.5V)	Qg	_	7.2	_					
Gate-Source Charge	Qgs	_	1.0	_	nC	$V_{GS} = 4.5V$, $V_{DS} = 10V$, $I_{D} = 6A$			
Gate-Drain Charge	Q_{gd}	_	1.9	_					
Turn-On Delay Time	t _{D(ON)}	_	4.69	_		$V_{DD} = 10V, V_{GEN} = 4.5V,$ $R_{GEN} = 1\Omega, I_D = 6.7A$			
Turn-On Rise Time	t _R	_	13.19	_	ns				
Turn-Off Delay Time	t _{D(OFF)}	_	22.10	_	110				
Turn-Off Fall Time	t _F	_	6.43	_					

Notes:

- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







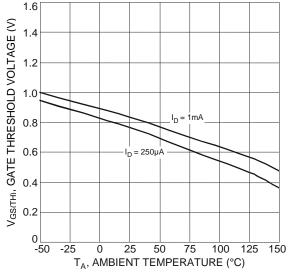
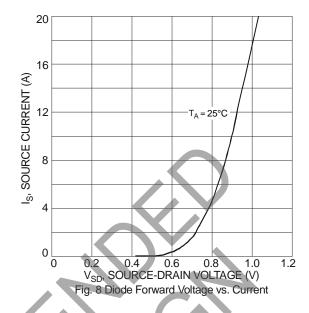
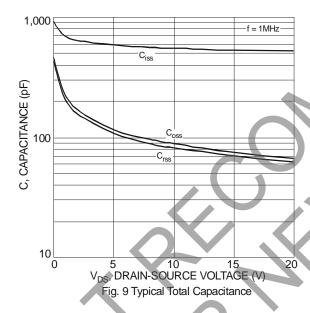


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





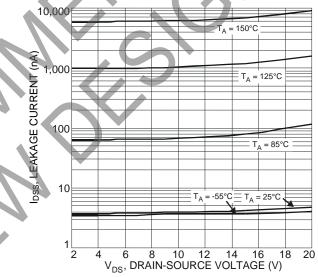


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

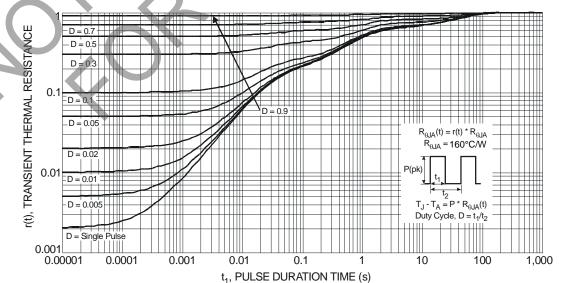


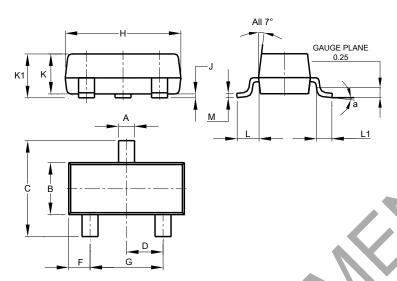
Fig. 11 Transient Thermal Response



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

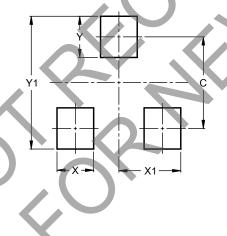


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
ם	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
H	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.





Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	29



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DMN2041L

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